Please amend the subject application as follows:

IN THE CLAIMS:

Please cancel claims 11-13 and 52-53 without prejudice, and accept amended claims 10, 49 and 51 as follows:

1-9. (canceled)

10. (currently amended) A contact structure of a wire, comprising:

a wire of a conductive material on a substrate, wherein the wire is made of a conductive material including aluminum-based material;

an inter-layer reaction layer formed on the wire and including at least silicon or transition metal, wherein the inter-layer reaction layer includes at least Al_xSi_x; and

a conductive layer electrically connected to the wire via the inter-reaction layer.

11. – 13. (canceled)

14. (original) The contact structure of claim 10, wherein the conductive layer is made of a transparent conductive material of indium zinc oxide.

15. (original) The contact structure of claim 10, further comprising an insulating layer having a contact hole exposing the inter-layer reaction layer between the wire and the conductive layer.

16. – 44. (canceled)

45. (previously presented) A thin film transistor array panel, comprising:

a gate wire made of a first conductive material on an insulating substrate;

a gate insulating layer covering the gate wire;

a semiconductor layer formed on the gate insulating layer;

a data wire made of a second conductive material on the gate insulating layer and the semiconductor layer;

a passivation layer covering the data wire;

an inter-layer reaction layer formed on the gate wire and the data wire; and

a transparent conductive layer pattern electrically connected to the gate wire or the data wire through a first contact hole of the gate insulating layer or the passivation layer via the first contact hole,

wherein the transparent conductive pattern is electrically connected to the gate wire or the data wire via the inter-layer reaction layer.

46. (original) The thin film transistor array panel of claim 45, wherein the first and second conductive material include a metal of aluminum-based material.

47. (original) The thin film transistor array panel of claim 45, wherein the insulating layer and the passivation layer are made of silicon-nitride.

48. (original) The thin film transistor array panel of claim 45, wherein the transparent conductive layer pattern is made of indium zinc oxide.

49. (currently amended) The thin film transistor array panel of claim 45, wherein the gate wire includes a gate line, a gate electrode connected to the gate line, and a gate pad which is connected to the gate line and receives a signal from an external circuit, and the data wire includes a data line, a source electrode connected to the data line, a drain electrode which is separated from the [[drain]] source electrode and opposite to the [[drain]] source electrode with respect to the gate electrode, and a data pad which is connected to the data line and receives a signal from a external circuit.

50. (original) The thin film transistor array panel of claim 45, wherein the inter-layer reaction layer includes silicon or transition metal.

51. (currently amended) A wiring contact structure, comprising:

a first wire formed of a conductive material, wherein the first wire contains aluminum; and

a second wire formed on and in contact with the first wire, the second wire comprising:

a first conductive layer formed of a conductive material; and

a second conductive layer sandwiched between the first wire and the first conductive layer and containing silicon or transition metal,

wherein the first conductive layer is electrically connected to the first wire via the second conductive layer, and the second conductive layer contains Al_xSi_x.

52. – 53. (canceled)

54. (previously presented) The wiring contact structure of claim 51, wherein the first conductive layer is formed of a transparent conductive material.